

Enhanced photonic stability of GaAs in aqueous electrolyte using alkanethiol self-assembled monolayers and post-processing with ammonium sulfide

Palani Arudra, Gregory M. Marshall, Neng Liu, and Jan J. Dubowski *

Laboratory for Quantum Semiconductors and Photon-based BioNanotechnology, Department of Electrical and Computer Engineering, Université de Sherbrooke, Sherbrooke, Québec J1K 2R1, Canada

* Author to whom correspondence should be addressed. Tel: 819-821-8000; Fax: 819- 821-7937; URL: <http://www.dubowski.ca>

SUPPORTING INFORMATION

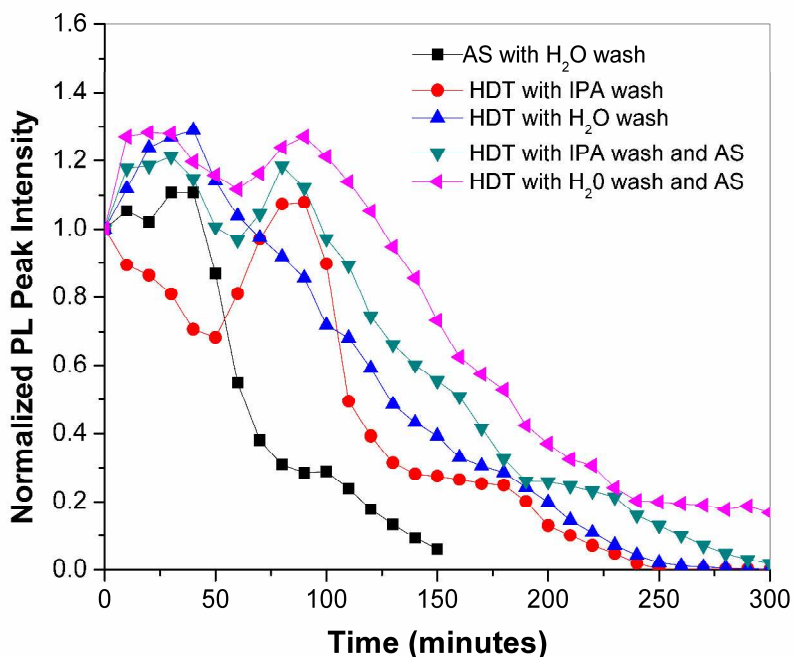
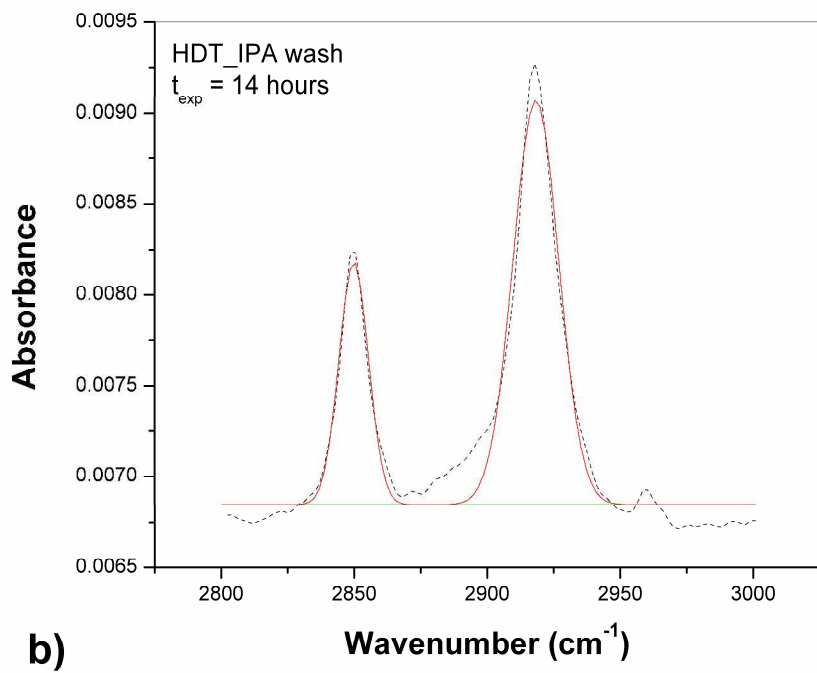
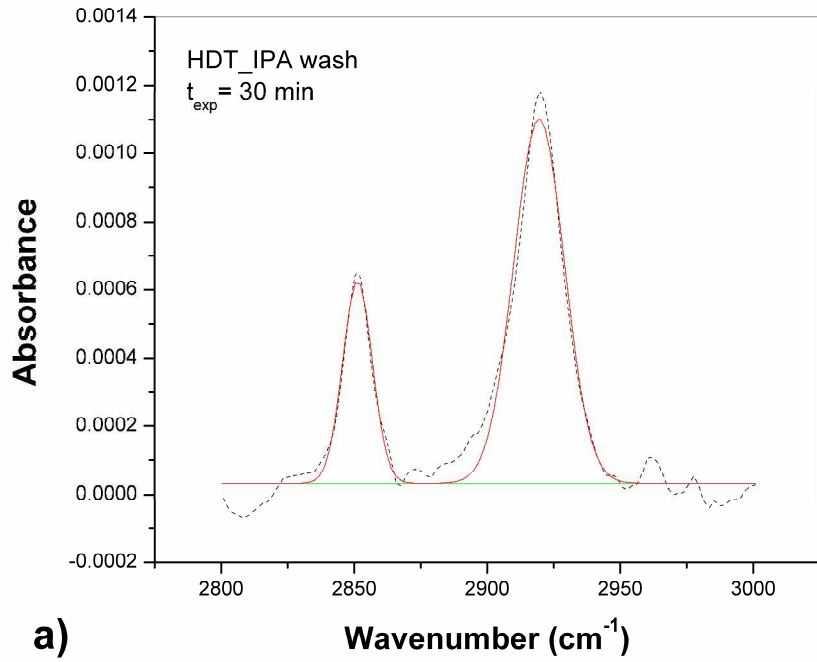
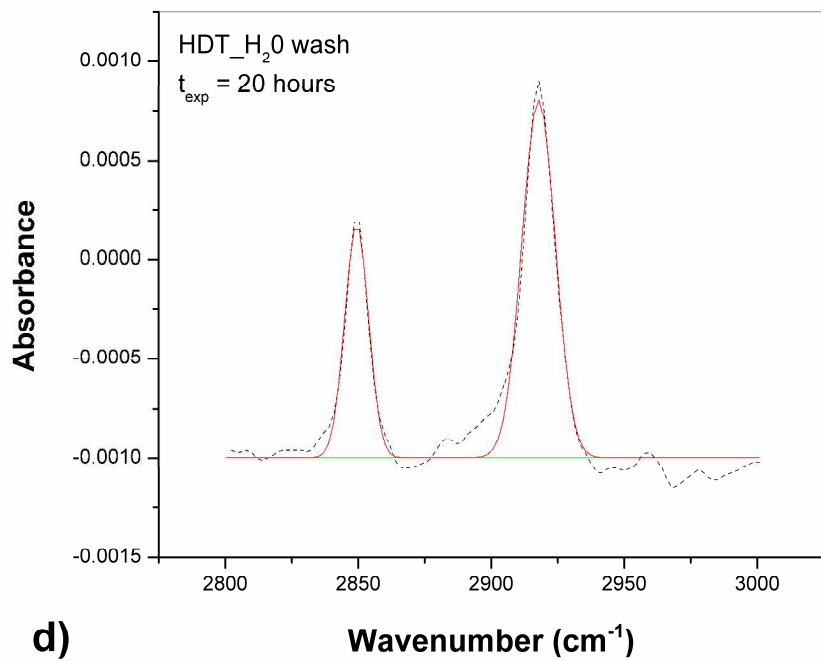
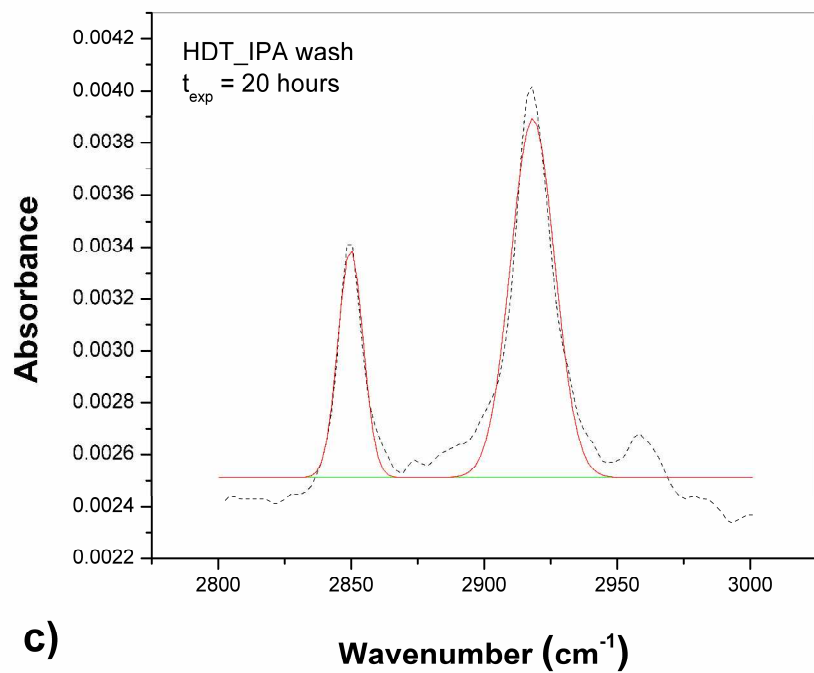


Figure S1. *In situ* PL intensity (I_{PL}) from processed GaAs samples immersed in PBS solution at pH 7.4. For each case, data are normalized to I_{PL} at $t = 0$.





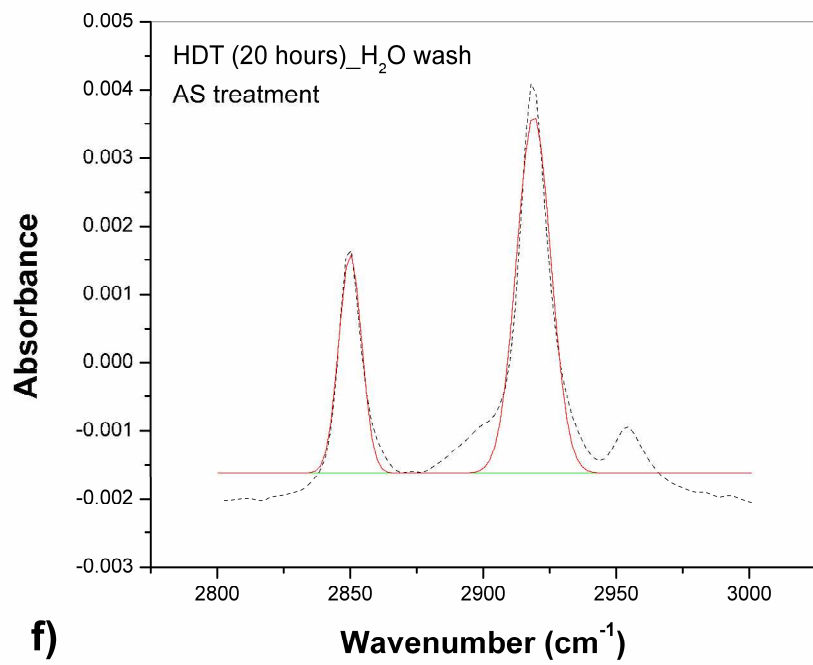
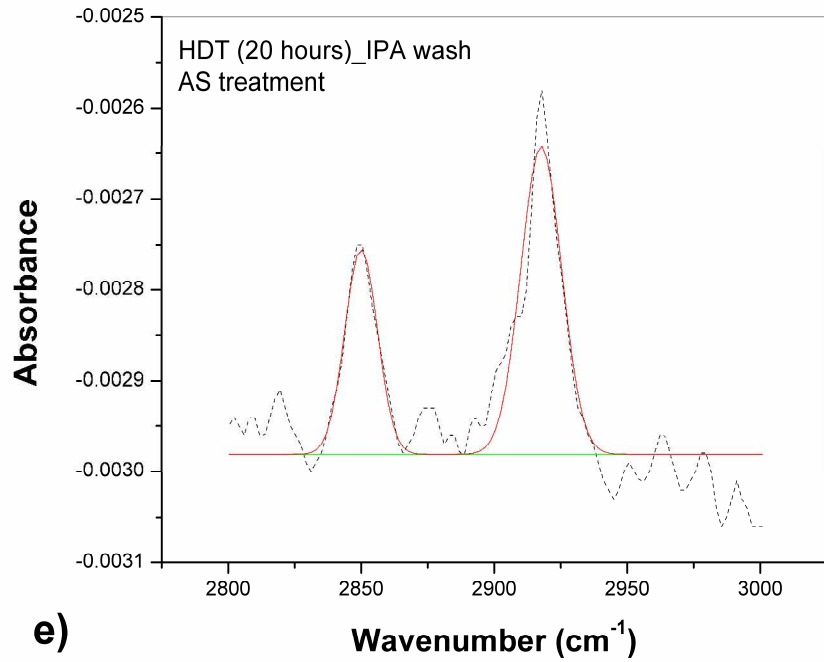


Figure S2. FTIR absorption spectra of HDT SAMs on GaAs surface washed with IPA (a, b, c, e) or H₂O (d, f) and followed by AS treatment (e, f).